

EAST - [10765100.wsp:1]

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1 and (nitride near buffer)

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	U	I	Document ID	Issue Date	Pages	Title	Current Off	Current XRef	
25	<input type="checkbox"/>	<input type="checkbox"/>	US 20030010993 A1	20030116	15	NITRIDE SEMICONDUCTOR DEVICE	257/99	257/E33.028; 257/E33.03	
26	<input type="checkbox"/>	<input type="checkbox"/>	US 20030006418 A1	20030109	13	Group III nitride based light emitting diode structures with a quantum well and superlattice, n-type III nitride based quantum well structures, and Method for growing high quality group-III nitride thin film by metal organic chemical vapor deposition	257/79	257/E33.008	
27	<input type="checkbox"/>	<input type="checkbox"/>	US 20020192373 A1	20021219	7		427/255.28		
28	<input type="checkbox"/>	<input type="checkbox"/>	US 20020179911 A1	20021205	11	Pendeoepitaxial gallium nitride semiconductor layers on silicon carbide substrates	257/77	257/615; 257/622; 257/628	
29	<input type="checkbox"/>	<input type="checkbox"/>	US 20020148534 A2	20021017	13	METHODS OF FABRICATING GALLIUM NITRIDE SEMICONDUCTOR LAYERS BY LATERAL OVERGROWTH THROUGH OFFSET MASKS	148/33	117/104; 257/E21.125; 438/931	
30	<input type="checkbox"/>	<input type="checkbox"/>	US 20020125491 A1	20020912	6	Semiconductor element	257/94	257/96; 257/E21.127	
31	<input type="checkbox"/>	<input type="checkbox"/>	US 20020111044 A1	20020815	13	Gallium nitride semiconductor structures fabricated by pendeoepitaxial methods of fabricating gallium nitride semiconductor layers on weak nodes	438/797	257/E21.127; 257/E21.131	
32	<input type="checkbox"/>	<input type="checkbox"/>	US 20020110997 A1	20020815	9	Methods of fabricating gallium nitride semiconductor layers on substrates including non-gallium nitride nodes	438/479	257/E21.125; 257/E21.127; 257/E21.131	
33	<input type="checkbox"/>	<input type="checkbox"/>	US 20020100412 A1	20020801	22	Low dislocation buffer and process for production thereof as well as device provided with low dislocation buffer	117/89	257/E21.125; 257/E21.127	
34	<input type="checkbox"/>	<input type="checkbox"/>	US 20020098693 A1	20020725	24	Single step pendeo- and lateral epitaxial overgrowth of group III-nitride epitaxial layers with n-type III-nitride buffer layer and resulting structure	438/687	257/E21.112; 257/E21.131	
35	<input type="checkbox"/>	<input type="checkbox"/>	US 20020078881 A1	20020627	43	Method and apparatus for producing M ^{III} N columns and M ^{III} N materials grown thereon	117/84	257/E21.097	